selectively implanting fluorine ions into a second part of the second region with a second ion-implantation condition. the second part of the second region being for the third MOSFET, the second ion-implantation condition being determined to form a third gate oxide film;

simultaneously growing oxide films on and over the first and second regions of the semiconductor substrate; and

A1 cont'd

forming the first to third MOSFETs by using the simultaneously grown oxide films, so that the first to third MOSFETs have the first to third gate oxide films, respectively, wherein the second gate oxide film is thicker than the first gate oxide film and the third gate oxide film is thicker than the first gate oxide film and is thinner than the second gate oxide film; and

wherein the threshold level of the first MOSFET is relatively low and the threshold levels of the second and third MOSFETs are relatively high, and the second MOSFET is an n-type and the third MOSFET is a p-type.

4. (Amended) A fabrication method as claimed in claim 3, wherein the first and second ion-implantation conditions are determined so that the third gate oxide film is thinner than the second gate oxide film.

- - 18. (Newly Added) The method of claim 3, wherein the second and third MOSFETs have equal gate-channel leakage current characteristics. - -

A2

A2 cont'd B1

- - 19. (Newly Added) The method of claim 18, wherein the standby current in each of the second and third MOSFETs do not depend on the gate-channel leakage current characterisics but on the subthreshold characteristics. - -